

005550-5684560

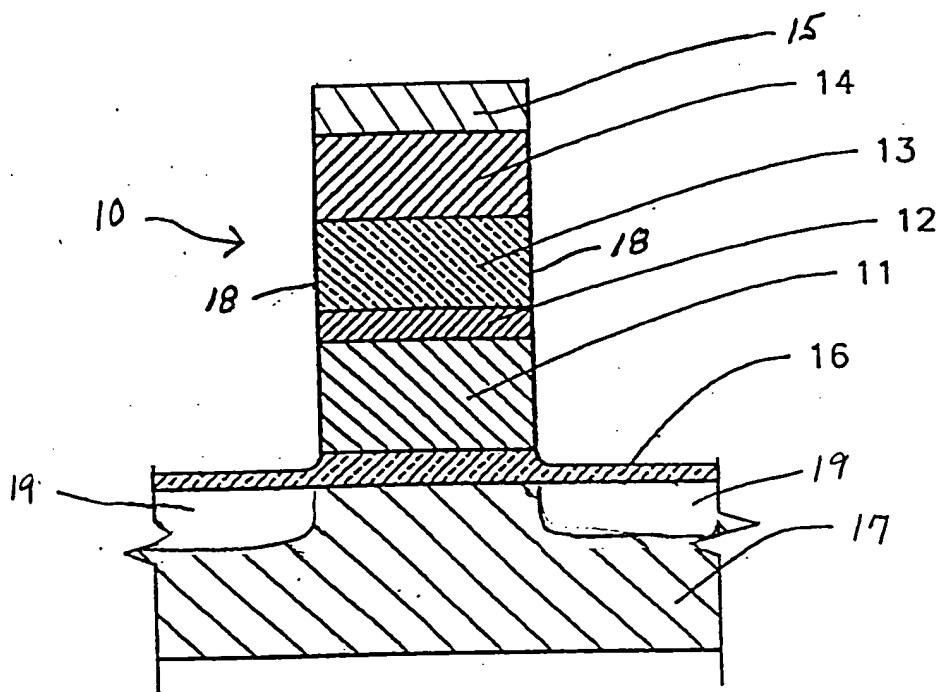


FIG. 1

A cross-sectional view of a multi-layered assembly 10. The assembly consists of a central core 11, surrounded by a layer 12, a layer 13, a layer 14, a layer 15, and a layer 16. The core 11 is shown with a diagonal hatching pattern. The layers 12, 13, 14, 15, and 16 are shown with different hatching patterns. The assembly 10 is mounted on a base 17, which is shown with a diagonal hatching pattern. A layer 19 is located between the assembly 10 and the base 17. A dimension line indicates the height h of the assembly 10. A dimension line indicates the thickness t of the assembly 10. A dashed line indicates the center of the assembly 10.

FIG. 2

005250-5622560

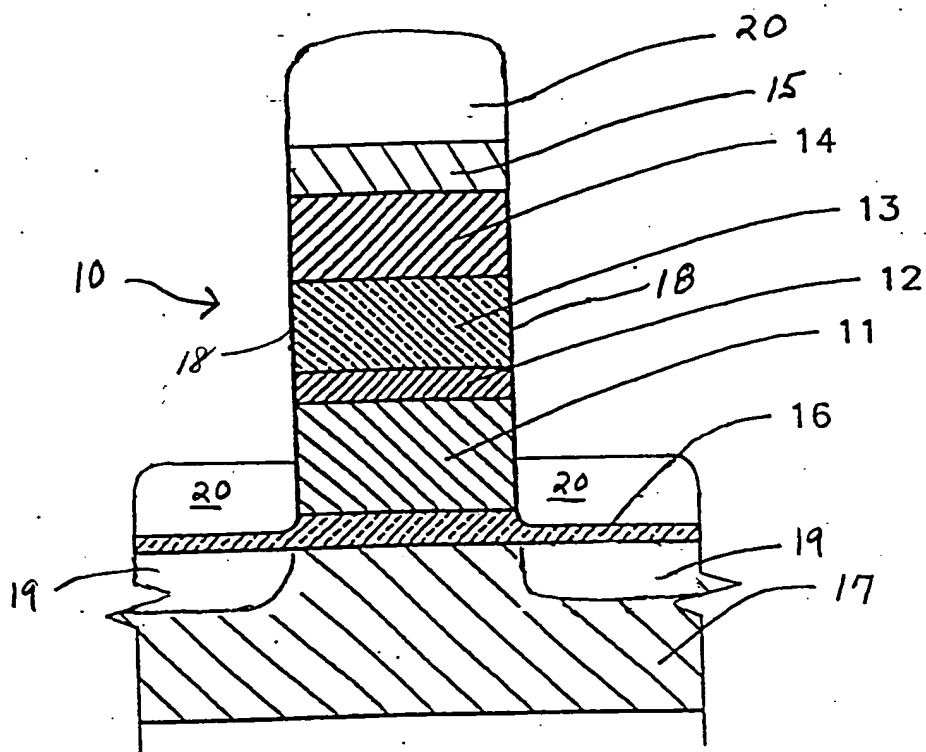


FIG. 3

005250-5844560

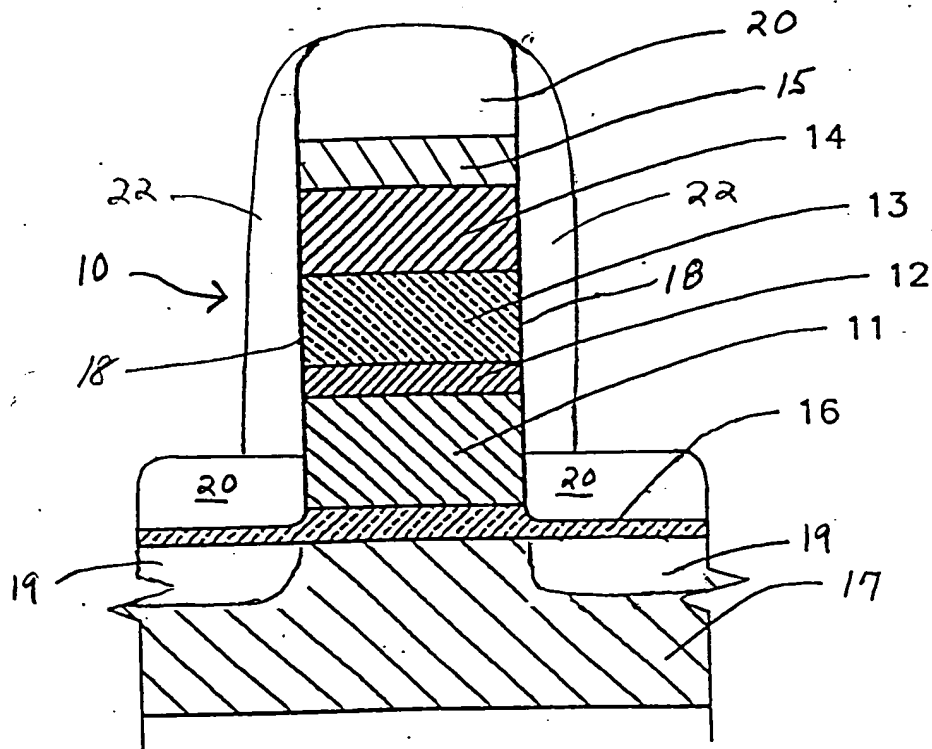


FIG. 4

A detailed cross-sectional diagram of a cylindrical device, likely a fuel cell or battery component. The device consists of several concentric layers. The outermost layer is labeled 10. Inside this is a layer labeled 11. The central core is composed of multiple layers, including 12, 13, 14, 15, 16, 17, 18, 19, and 20. A central vertical channel or passage is labeled 22. The device is shown mounted on a base or support structure, with a flange or seal labeled 19. Arrows indicate the flow of a gas, labeled O_2 , into the device from the left and right sides. The diagram uses various hatching patterns to distinguish between different materials or layers.

FIG. 5

005785-05400

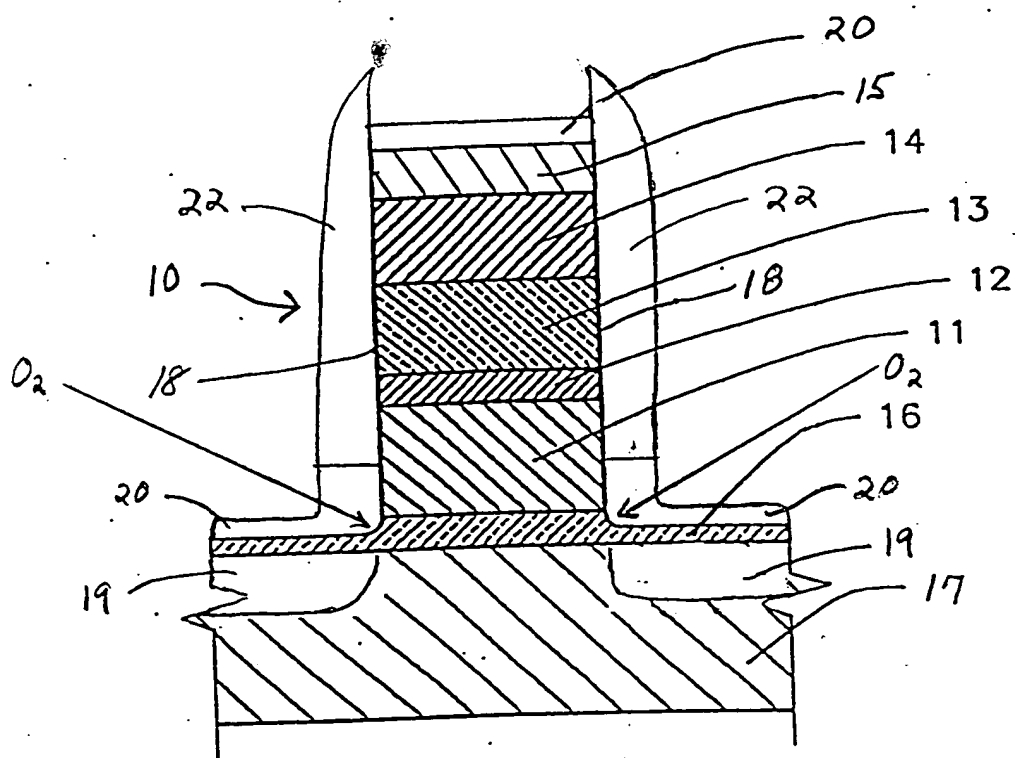


FIG. 6

A detailed cross-sectional diagram of a multi-layered structure. The structure consists of several horizontal layers with different hatching patterns. From top to bottom, the layers are labeled: 15 (topmost, white), 14 (hatched with diagonal lines), 22 (hatched with diagonal lines), 13 (hatched with diagonal lines), 18 (hatched with diagonal lines), 12 (hatched with diagonal lines), 11 (hatched with diagonal lines), and 0₂ (bottommost, white). The entire stack is flanked by two vertical, curved structures labeled 10 and 22. Below the stack, there is a horizontal layer labeled 19, which is flanked by two curved structures labeled 17 and 16. The entire assembly is supported by a base labeled 18. The label 0₂ is also present near the bottom of the stack.

FIG. 7

005350-5564560

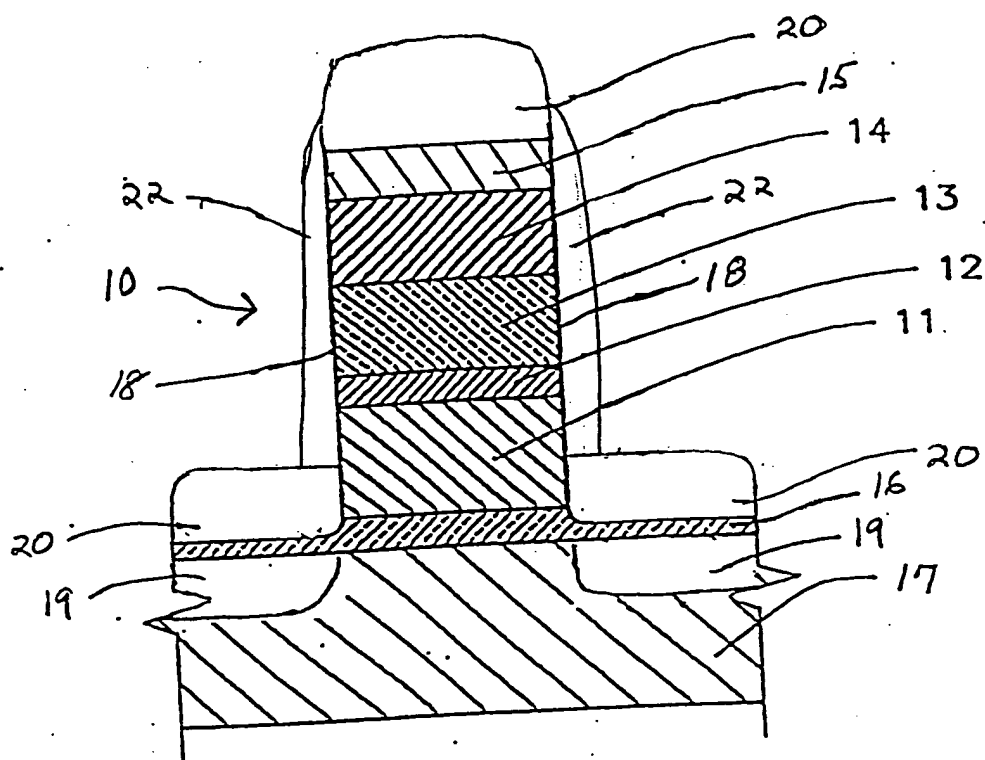


FIG. 8

005250-5604560

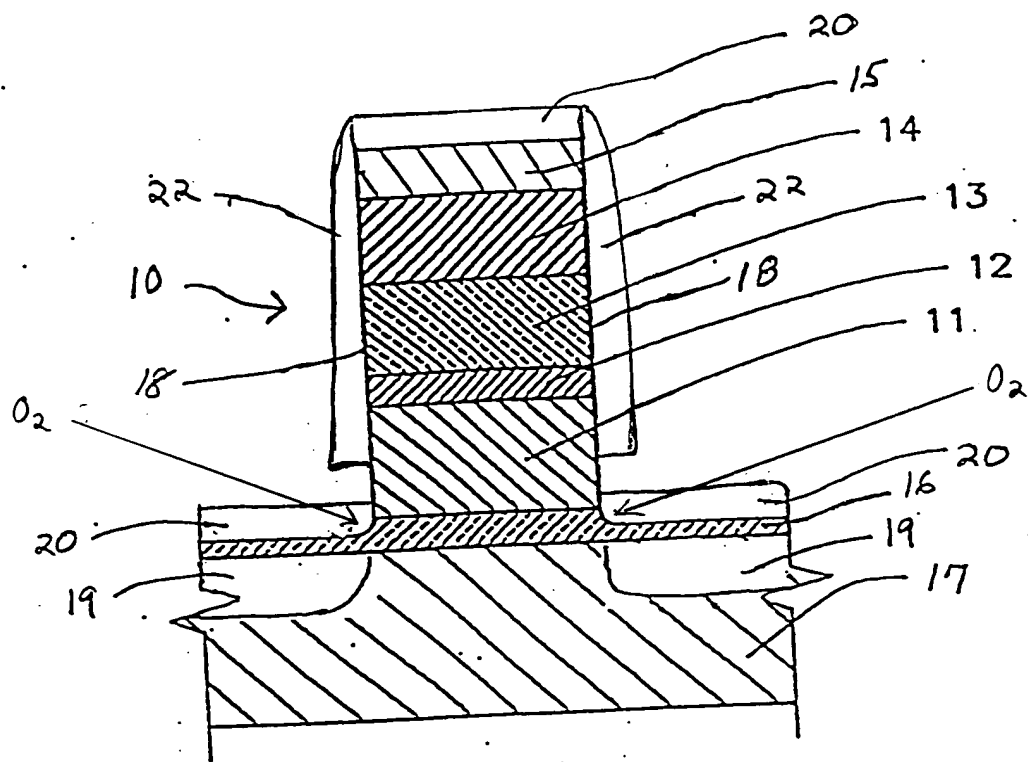


FIG. 9

FORM GATE DIELECTRIC ON UPPER SURFACE OF
SUBSTRATE



FORM WORD LINE STACK WITH CONDUCTIVE BARRIER
AND/OR METAL LAYERS OVER GATE DIELECTRIC



FORM OXIDE LAYER OVER SURFACE OF WAFER



OPTIONALLY REMOVE THIN OXIDE LAYER FROM
SIDEWALLS OF WORD LINE STACK



FORM NITRIDE SPACERS ALONG SIDEWALLS/EDGES OF
BARRIER LAYER AND METAL LAYER OF WORD LINE
STACK



OPTIONALLY REMOVE PART OR ALL OF THE OXIDE LAYER FROM
SURFACE OF WAFER



PERFORM SOURCE/DRAIN REOXIDATION

FIG. 10

005250 5662560

0057835-05500

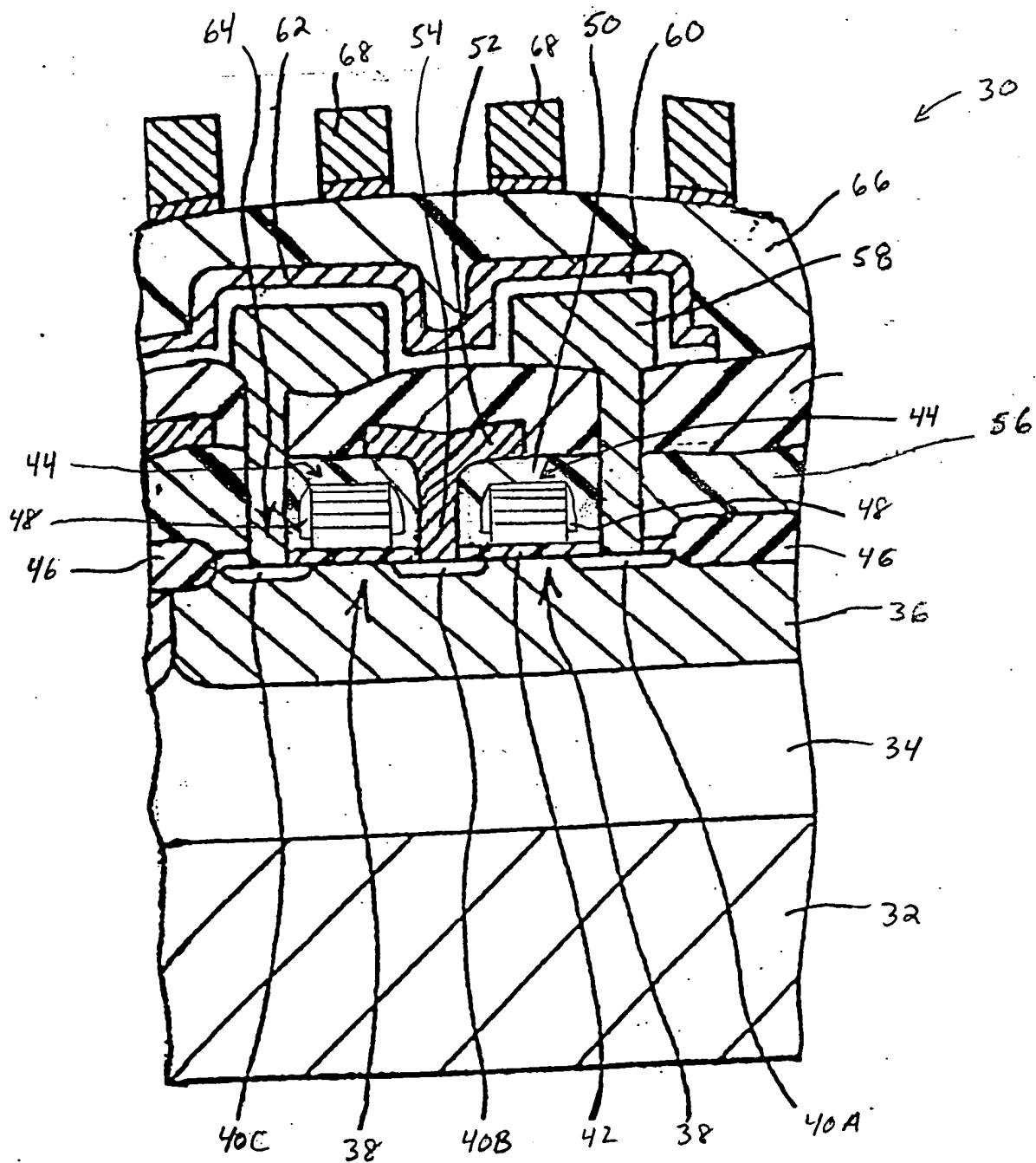


FIG. 11